





**European Research Council** 

# Silicon Undulator Prototype: manufacturing and X-ray Characterization

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### Outline

- Why a crystalline undulator?
- Manufacturing techniques
  - The sandblasting method
  - The grooving method
- Conclusions

### Classic free electron lasers

### Why a crystalline undulator?

Manufacturing techniques

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Conclusions

Electron / positron source



 $\lambda lu \rightarrow Undulation period$ Current limit ~10 mm  $\lambda lph = \lambda lu /2\gamma T_2 (1+KT_2/2)$ 

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## Crystalline undulators

#### Why a crystalline undulator?

Manufacturing techniques

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The grooving method

Charged

- Particle beam Crystals are capable of channel charged particles impinging at small angle wrt lattice planes (channeling).
- If the lattice planes are bent, the strong electric potential • induces channeled particles to follow the crystal curvature.
- A crystal periodically bent could induce a motion similar to • a conventional magnetic undulator, with lower  $\lambda \downarrow u$ .

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### Manufacturing techniques

Why a crystalline undulator?

### Manufacturing techniques

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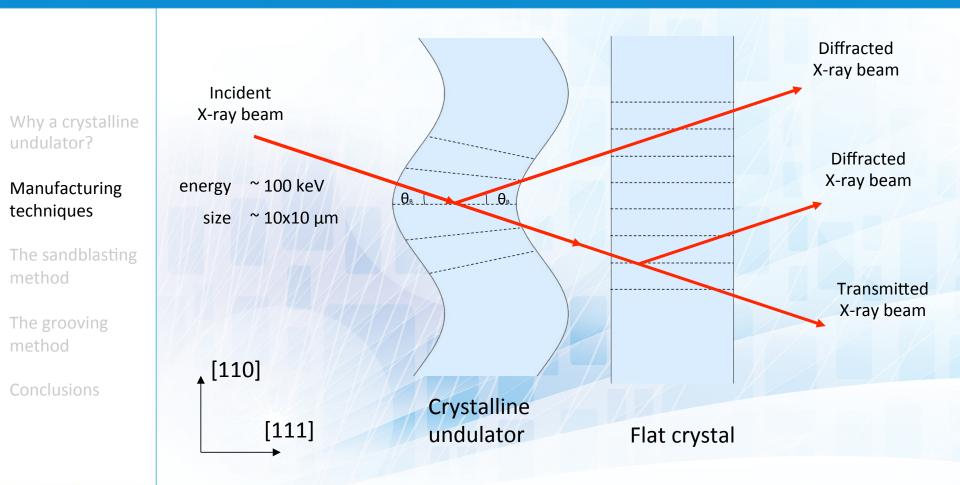
Conclusions

- We decided to manufacture CU made of silicon, because it is a material with a high crystalline order, easy to work.
- Only mechanical techniques have been used, to study the possibilities of such methods. The deformation is selfstanding.
- If only mechanical means are used, no contaminating elements are deposited on the CUs.



### Hard X-ray measurement

#### Measurements performed at ESRF and ILL (Grenoble, France)



# Sandblasting method

Why a crystalline undulator?

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Conclusions

- The sandb layer on the
- The amorphized layer behaves as a thin compressive film, causing the curvature of the substrate.

Width

• To obtain an undulated deformation, both faces must be patterned, with a phase shift of half a period.

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Thickness

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ng an amorphized

# Sandblasting method

Why a crystalline undulator?

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Conclusions

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Method	Sandblasting	
Material	Silicon (111)	tt (/rua
Thickness	1.0 mm	
Length	8.0 mm	Angular shift (Jrrad) -50 $+$ $+$ $+$ $+$ $+$ $+$ $+$ $+$ $+$ $+$
Width	10.0 mm	
Period ( $\lambda \downarrow u$ )	2.0 mm	
Number of periods	4	
Amplitude	23 nm	Dosition
Analysed through at the DIGRA facilit Grenoble (France)		-20 $-10$ $-20$
amattari et al. J. Appl. Cryst. 50 (	FOR SCIENCE	Length (mm)

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# Sandblasting method

Why a crystalline undulator?

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### The sandblasting method

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#### Advantages

- No Contaminants
- Adjustable
- Easy and economic
- Fast

### Disadvantages

- Crystal damage
- The period  $(\lambda \downarrow u)$  is limited to be not smaller than ~ 1 mm



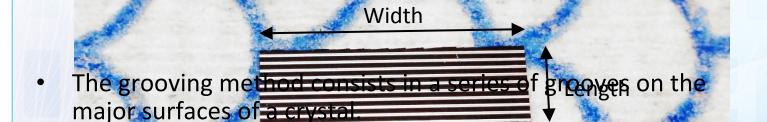
Why a crystalline undulator?

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- It was shown that a series of grooves may cause a permanent and reproducible deformation of the whole sample.
- A crystalline undulator can be realized by making an alternate pattern of parallel grooves on both the surfaces of a crystal, with a phase shift of half a period.

Camattari et al Meccanica 48 (2013) 1875-1882

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Why a crystalline undulator?

Bagli

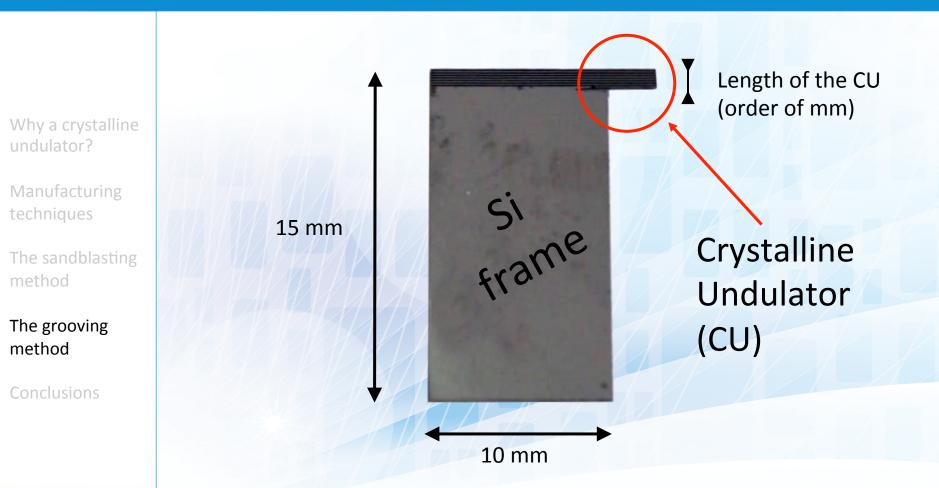
Manufacturing techniques

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Method	Grooving	
Material	Silicon (111)	Angular shift (Jurad)
Thickness	0.2 mm	
Length	5.0 mm	
Width	45.0 mm	
Period ( $\lambda \downarrow u$ )	1.0 mm	
Number of periods	5	
Amplitude	4.1 nm	
Analysed through at the ID15 facility Grenoble (France)		$ \begin{array}{c c} \hline \\ \hline $
Bagli et al. Eur. Phys. J. C 74 (2014	Length (mm)	

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Why	a crystallin	е
undu	lator?	

Manufacturing techniques

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Method	Grooving					
Material	Silicon (111)					
Thickness	0.2 mm					
Length	3.34 mm					
Width	10.0 mm					
Period ( $\lambda \downarrow u$ )	0.334 mm					
Number of periods	10					
Amplitude	1.28 nm					
Angalysed through hard X-rays						
at the ID11 fatilit	ty, ESRP,	<b>5</b> 2.0 2.5 3.0				
Grenoble (France	e)	ngth (mm)				
Prelaminar results	ESE	<u>KF</u>				

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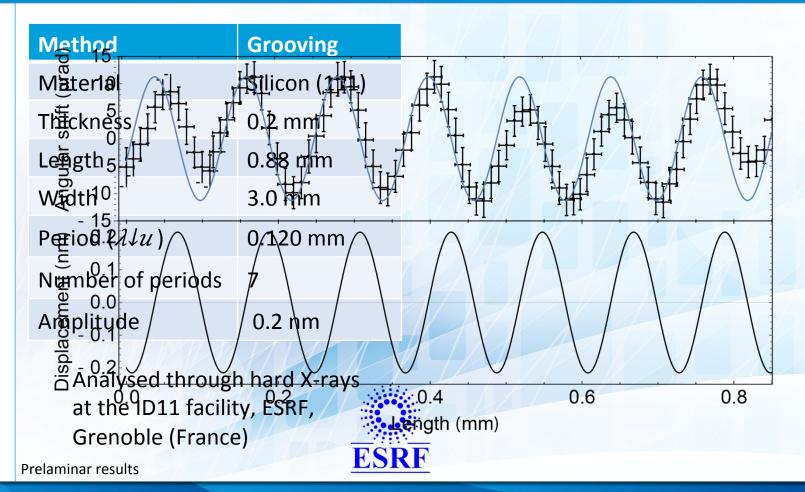
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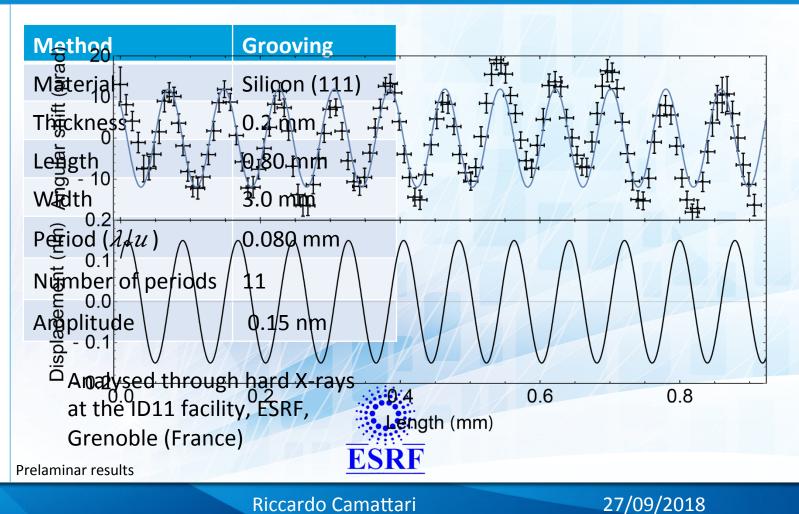


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### Advantages

- No Contaminants
- Adjustable
- The period can be as small as the blade width

### Disadvantages

Crystal damage



### Method comparison

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Sandblasting method		Grooving method	
No contaminants	1	No contaminants	1
Adjustable	1	Adjustable	1
Higher period	Ļ	Smaller period	1
Less crystal damage	1	More crystal damage	Ļ

### Conclusions

Why a crystalline undulator?

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Conclusions

- Self-standing undulated crystals have been realized.
  - It is possible to decrease the period, but it decreases also the undulating amplitude.
- The smallest period was obtained with the grooving method, namely 80 µm with 0.15 nm of amplitude.
- Test with charged particles are fundamental for evaluating the crystal damage.

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